TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET TIM1414-4LA PRELIMINARY

FEATURES

- **HIGH POWERT**
 - P1dB=36.5dBm at 14.0GHz to 14.5GHz
- **HIGH GAIN**

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G1dB=6.5dB at 14.0GHz to 14.5GHz

- BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB	P1dB		dBm	36.0	36.5	
Compression Point					- N	5,000
Power Gain at 1dB	G1dB	VDS= 9V	dB	6.0	6.5	COM
Compression Point		f= 14.0 to 14.5GHz	THE .	Track Williams	.075	
Drain Current	IDS1	100 T.P.	Α	_	1.7	2.2
Gain Flatness	ΔG		dB		—	±0.8
Power Added Efficiency	ηadd	MI	%		23	
3 rd Order Intermodulation	IM3		dBc	-42	-45	
Distortion		NOTE				
Drain Current	IDS2		Α		1.7	2.2
Channel Temperature Rise	∆Tch	VDS X IDS X Rth(c-c)	°C		-51	70

NOTE: Two Tone Test, Po=25dBm (Single Carrier Level)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V	mS		1200	
		IDS= 2.0A				-
Pinch-off Voltage	VGSoff	VDS= 3V	V	-2.0	-3.5	-5.0
		IDS= 60mA		13 -1	We'c	COM
Saturated Drain Current	IDSS	VDS= 3V	Α	WWW	4.0	5.2
		VGS= 0V		-		
Gate-Source Breakdown	VGSO	IGS= -60μA	V	-5	_	
Voltage	TOM	144				
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	2.9	3.5

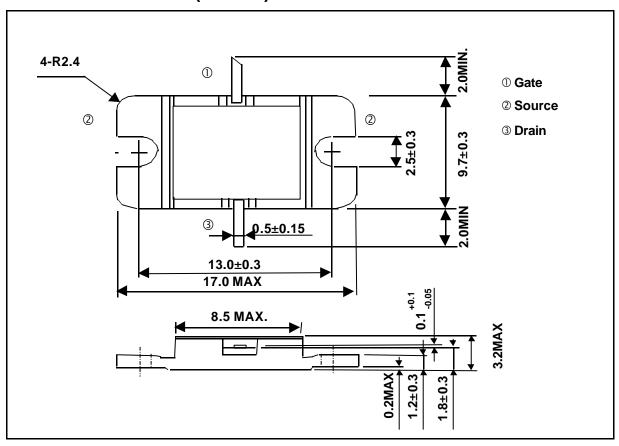
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The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	Α	5.2
Total Power Dissipation (Tc= 25 °C)	PT	W	30
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-9D1B)



HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260° C.